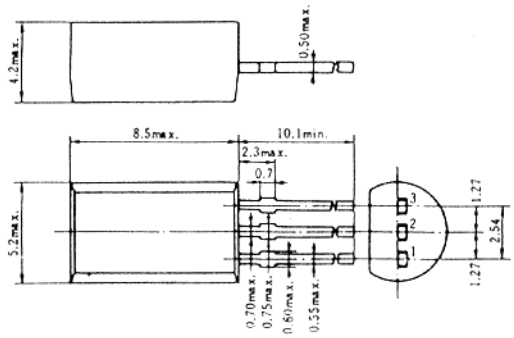
HITACHI

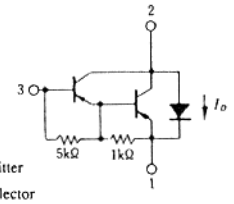
2SB1387

SILICON PNP EPITAXIAL

LOW FREQUENCY POWER AMPLIFIER
Complementary pair with 2SD1978



(JEDEC TO-92 MOD.)



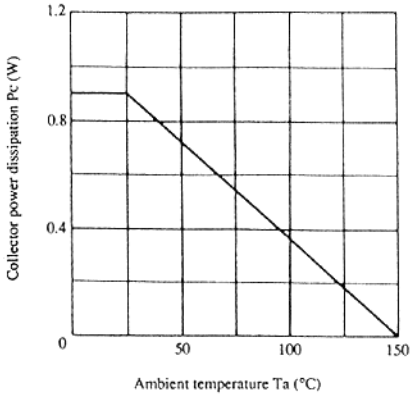
1. Emitter
2. Collector
3. Base

(Dimensions in mm)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SB1387	Unit
Collector to base voltage	V_{CBO}	−120	V
Collector to emitter voltage	V_{CEO}	−120	V
Emitter to base voltage	V_{EBO}	−7	V
Collector current	I_C	−1.5	A
Collector peak current	$i_{C(peak)}$	−3.0	A
C to E diode forward current	I_D	1.5	A
Collector power dissipation	P_C	0.9	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION CURVE



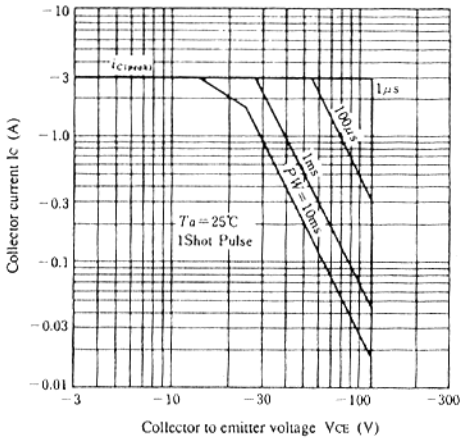
■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	I_C = −0.1mA, I_E = 0	−120	—	—	V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	I_C = −10mA, R_{BE} = ∞	−120	—	—	V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	I_E = −50mA, I_C = 0	−7	—	—	V
Collector cutoff current	I_{CBO}	V_{CB} = −100V, I_E = 0	—	—	−1	μA
	I_{CEO}	V_{CE} = −100V, R_{BE} = ∞	—	—	−10	μA
DC current transfer ratio	h_{FE}	V_{CE} = −3V, I_C = −1A*	2000	—	10000	
Collector to emitter saturation voltage	$V_{CE(sat)1}$	I_C = −1A, I_B = −1mA*	—	—	−1.5	V
	$V_{CE(sat)2}$	I_C = −1.5A, I_B = −1.5mA*	—	—	−2.0	V
Base to emitter saturation voltage	$V_{BE(sat)1}$	I_C = −1A, I_B = −1mA*	—	—	−2.0	V
	$V_{BE(sat)2}$	I_C = −1.5A, I_B = −1.5mA*	—	—	−2.5	V
C to E diode forward voltage	V_D	I_D = 1.5A*	—	—	3.0	V

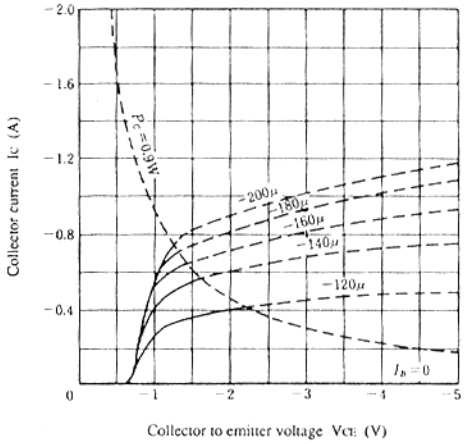
* Pulse Test

2SB1387

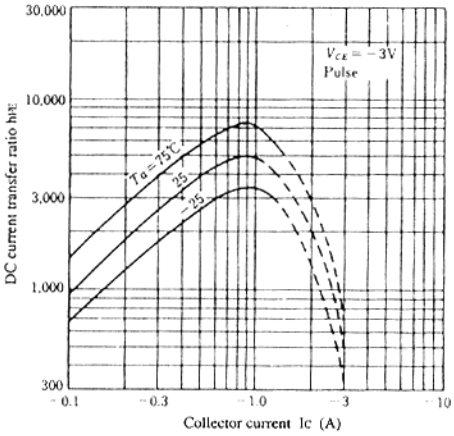
AREA OF SAFE OPERATION



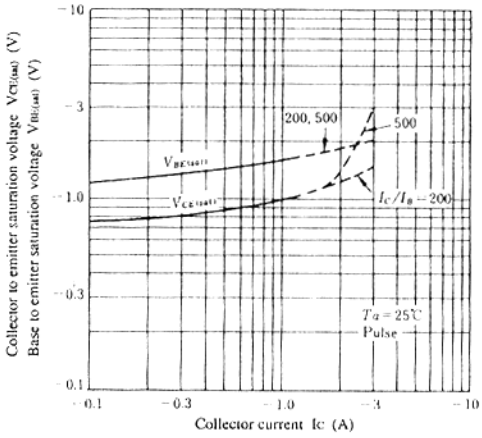
TYPICAL OUTPUT CHARACTERISTICS



DC CURRENT TRANSFER RATIO VS. COLLECTOR CURRENT



SATURATION VOLTAGE VS. COLLECTOR CURRENT



TRANSIENT THERMAL RESISTANCE